

IN THE CLAIMS

Per the revised amendment practice, a complete listing of all claims in the application follows.

Claims 1-26 (cancelled).

27. (Previously presented) A method of establishing electrical contact between a semiconductor substrate and a semiconductor device, comprising:

- covering said substrate with an insulating layer;
- etching a hole through said insulating layer to said substrate;
- partially plugging said hole with doped polycrystalline silicon;
- depositing at least one metal layer within said hole over said doped polycrystalline silicon;
- siliciding said at least one metal layer, wherein said step of siliciding said at least one metal layer comprises siliciding a titanium layer;
- nitridizing said at least one metal layer, wherein said step of nitridizing said at least one metal layer comprises nitridizing a non-titanium layer; and
- forming said semiconductor device over said at least one metal layer, wherein said step of forming said semiconductor device further comprises forming said semiconductor device over said non-titanium layer.

Claims 28-72 (Cancelled).